

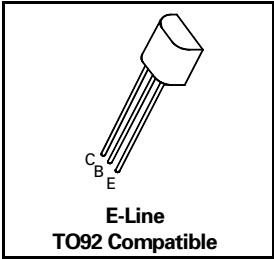
NPN SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

ZTX458

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FEATURES

- * 400 Volt V_{CEO}
- * 0.5 Amp continuous current
- * P_{tot} = 1 Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	300	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	400			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{CEO(sus)}$	400			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=320V$
Collector Cut-Off Current	I_{CES}			100	nA	$V_{CE}=320V$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.2 0.5	V V	$I_C=20mA, I_B=2mA$ $I_C=50mA, I_B=6mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=50mA, I_B=5mA$
Base-Emitter Turn On Voltage	$V_{BE(on)}$			0.9	V	$I_C=50mA, V_{CE}=10V$
Static Forward Current Transfer Ratio	h_{FE}	100 100 15		300		$I_C=1mA, V_{CE}=10V$ $I_C=50mA, V_{CE}=10V$ $I_C=100mA, V_{CE}=10V^*$
Transition Frequency	f_T	50			MHz	$I_C=10mA, V_{CE}=20V$ $f=20MHz$
Collector-Base Breakdown Voltage	C_{obo}			5	pF	$V_{CB}=20V, f=1MHz$

TYPICAL CHARACTERISTICS

